

## ABSTRACT OF THE INVENTION

The present invention relates to a ferroelectric polymer storage device including at least two stacked ferroelectric polymer memory structures that are arrayed next to at least two respective stacked topologies that are a pre-fabricated silicon substrate cavity that includes interlayer dielectric layers and via structures. Combining ferroelectric polymer and ferroelectric oxide layers on the pre-fabricated silicon substrate cavity forms a multi-rank structure.

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